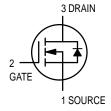
# **TMOS FET Transistor**

# N-Channel — Enhancement



#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit	
Drain Source Voltage	V <sub>DSS</sub>	60	Vdc	
Drain–Gate Voltage (R <sub>GS</sub> = 1.0 MΩ)	V <sub>DGR</sub>	60	Vdc	
Gate–Source Voltage — Continuous — Non–repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±40	Vdc Vpk	
Drain Current Continuous Pulsed	I <sub>D</sub>	200 500	mAdc	
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C	
Operating and Storage Temperature Range	TJ, Tstg	-55 to +150	°C	

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	TL	300	°C

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Drain–Source Breakdown Voltage (V <sub>GS</sub> = 0, I <sub>D</sub> = 10 µAdc)	V(BR)DSS	60	_	Vdc	
Zero Gate Voltage Drain Current (VDS = 48 Vdc, VGS = 0) (VDS = 48 Vdc, VGS = 0, TJ = 125°C)	IDSS		1.0 1.0	μAdc mAdc	
Gate-Body Leakage Current, Forward (VGSF = 15 Vdc, VDS = 0)	IGSSF	_	-10	nAdc	
ON CHARACTERISTICS <sup>(1)</sup>					
Gate Threshold Voltage (VDS = VGS, ID = 1.0 mAdc)	V <sub>GS(th)</sub>	0.8	3.0	Vdc	
Static Drain–Source On–Resistance (VGS = 10 Vdc, $I_D$ = 0.5 Adc) (VGS = 4.5 Vdc, $I_D$ = 75 mAdc)	rDS(on)		5.0 6.0	Ohm	
Drain-Source On-Voltage (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 0.5 Adc) (V <sub>GS</sub> = 4.5 Vdc, I <sub>D</sub> = 75 mAdc)	V <sub>DS(on)</sub>		2.5 0.45	Vdc	

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 3



Motorola Preferred Device



### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted) (Continued)

Ch	Symbol	Min	Max	Unit	
ON CHARACTERISTICS <sup>(1)</sup> (continued)					
On–State Drain Current (V <sub>GS</sub> = 4.5 Vdc, V <sub>DS</sub> = 10 Vdc)		I <sub>d(on)</sub>	75	_	mAdc
Forward Transconductance (VDS = 10 Vdc, ID = 200 mAd	9fs	100	_	μmhos	
DYNAMIC CHARACTERISTICS					
Input Capacitance		C <sub>iss</sub>	_	60	pF
Output Capacitance	$(V_{DS} = 25 \text{ V}, V_{GS} = 0, \\ f = 1.0 \text{ MHz})$	C <sub>oss</sub>	_	25	
Reverse Transfer Capacitance	- ,	C <sub>rss</sub>	_	5.0	
SWITCHING CHARACTERISTICS(1)					
Turn-On Delay Time	(V <sub>DD</sub> = 15 V, I <sub>D</sub> = 500 mA,	t <sub>on</sub>	_	10	ns
Turn-Off Delay Time	$R_{gen} = 25 \text{ ohms}, R_L = 25 \text{ ohms})$	t <sub>off</sub>	_	10	

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

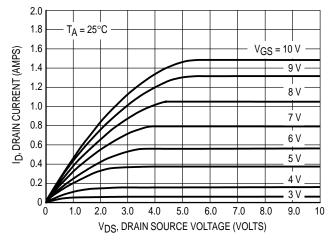


Figure 1. Ohmic Region

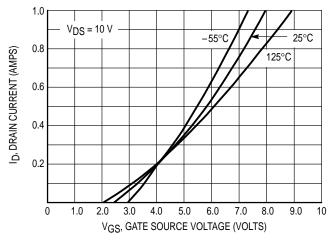


Figure 2. Transfer Characteristics

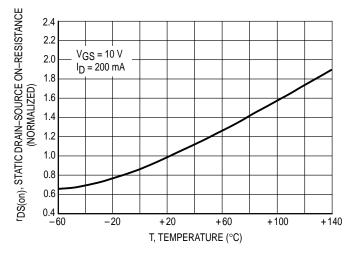


Figure 3. Temperature versus Static Drain–Source On–Resistance

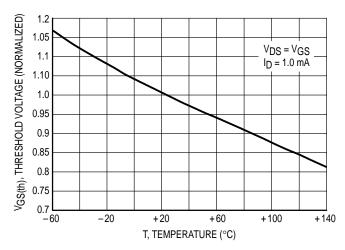
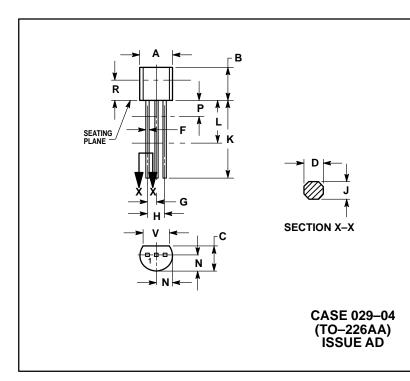


Figure 4. Temperature versus Gate Threshold Voltage

### **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
ν	0.135		3 43	

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

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